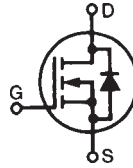


### X-Class HiPerFET™ Power MOSFET

**IXFT30N60X**  
**IXFQ30N60X**  
**IXFH30N60X**

$$\begin{aligned} V_{DSS} &= 600V \\ I_{D25} &= 30A \\ R_{DS(on)} &\leq 155m\Omega \end{aligned}$$

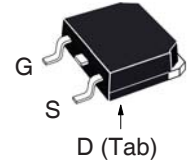
N-Channel Enhancement Mode  
Avalanche Rated  
Fast Intrinsic Diode



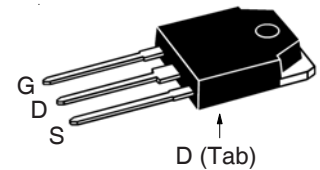
| Symbol     | Test Conditions                                                          | Maximum Ratings |                  |
|------------|--------------------------------------------------------------------------|-----------------|------------------|
| $V_{DSS}$  | $T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$                          | 600             | V                |
| $V_{DGR}$  | $T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$ , $R_{GS} = 1M\Omega$    | 600             | V                |
| $V_{GSS}$  | Continuous                                                               | $\pm 30$        | V                |
| $V_{GSM}$  | Transient                                                                | $\pm 40$        | V                |
| $I_{D25}$  | $T_C = 25^\circ\text{C}$                                                 | 30              | A                |
| $I_{DM}$   | $T_C = 25^\circ\text{C}$ , Pulse Width Limited by $T_{JM}$               | 60              | A                |
| $I_A$      | $T_C = 25^\circ\text{C}$                                                 | 10              | A                |
| $E_{AS}$   | $T_C = 25^\circ\text{C}$                                                 | 1               | J                |
| $dv/dt$    | $I_S \leq I_{DM}$ , $V_{DD} \leq V_{DSS}$ , $T_J \leq 150^\circ\text{C}$ | 50              | V/ns             |
| $P_D$      | $T_C = 25^\circ\text{C}$                                                 | 500             | W                |
| $T_J$      |                                                                          | -55 ... +150    | $^\circ\text{C}$ |
| $T_{JM}$   |                                                                          | 150             | $^\circ\text{C}$ |
| $T_{stg}$  |                                                                          | -55 ... +150    | $^\circ\text{C}$ |
| $T_L$      | Maximum Lead Temperature for Soldering                                   | 300             | $^\circ\text{C}$ |
| $T_{SOLD}$ | 1.6 mm (0.062in.) from Case for 10s                                      | 260             | $^\circ\text{C}$ |
| $M_d$      | Mounting Torque (TO-247 & TO-3P)                                         | 1.13 / 10       | Nm/lb.in         |
| Weight     | TO-268                                                                   | 4.0             | g                |
|            | TO-3P                                                                    | 5.5             | g                |
|            | TO-247                                                                   | 6.0             | g                |

| Symbol       | Test Conditions<br>( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified) | Characteristic Values |      |                                       |
|--------------|-----------------------------------------------------------------------------|-----------------------|------|---------------------------------------|
|              |                                                                             | Min.                  | Typ. | Max.                                  |
| $BV_{DSS}$   | $V_{GS} = 0V$ , $I_D = 1mA$                                                 | 600                   |      | V                                     |
| $V_{GS(th)}$ | $V_{DS} = V_{GS}$ , $I_D = 4mA$                                             | 2.5                   |      | 4.5 V                                 |
| $I_{GSS}$    | $V_{GS} = \pm 30V$ , $V_{DS} = 0V$                                          |                       |      | $\pm 100$ nA                          |
| $I_{DSS}$    | $V_{DS} = V_{DSS}$ , $V_{GS} = 0V$<br>$T_J = 125^\circ\text{C}$             |                       |      | 25 $\mu\text{A}$<br>750 $\mu\text{A}$ |
| $R_{DS(on)}$ | $V_{GS} = 10V$ , $I_D = 0.5 \cdot I_{D25}$ , Note 1                         |                       |      | 155 m $\Omega$                        |

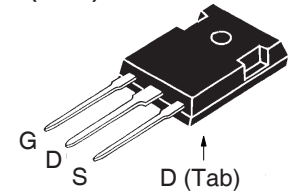
TO-268 (IXFT)



TO-3P (IXFQ)



TO-247 (IXFH)



G = Gate      D = Drain  
S = Source    Tab = Drain

### Features

- International Standard Packages
- Low  $R_{DS(on)}$  and  $Q_G$
- Avalanche Rated
- Low Package Inductance

### Advantages

- High Power Density
- Easy to Mount
- Space Savings

### Applications

- Switch-Mode and Resonant-Mode Power Supplies
- DC-DC Converters
- PFC Circuits
- AC and DC Motor Drives
- Robotics and Servo Controls

| Symbol                              | Test Conditions<br>(T <sub>J</sub> = 25°C, Unless Otherwise Specified)                                                                                                          | Characteristic Values                                            |      |           |
|-------------------------------------|---------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|------------------------------------------------------------------|------|-----------|
|                                     |                                                                                                                                                                                 | Min.                                                             | Typ. | Max       |
| <b>g<sub>fs</sub></b>               | V <sub>DS</sub> = 10V, I <sub>D</sub> = 0.5 • I <sub>D25</sub> , Note 1                                                                                                         | 10                                                               | 17   | S         |
| <b>R<sub>Gi</sub></b>               | Gate Input Resistance                                                                                                                                                           |                                                                  | 2.6  | Ω         |
| <b>C<sub>iss</sub></b>              | V <sub>GS</sub> = 0V, V <sub>DS</sub> = 25V, f = 1MHz                                                                                                                           |                                                                  | 2270 | pF        |
| <b>C<sub>oss</sub></b>              |                                                                                                                                                                                 |                                                                  | 1610 | pF        |
| <b>C<sub>rss</sub></b>              |                                                                                                                                                                                 |                                                                  | 14   | pF        |
| <b>Effective Output Capacitance</b> |                                                                                                                                                                                 |                                                                  |      |           |
| <b>C<sub>o(er)</sub></b>            | Energy related                                                                                                                                                                  | V <sub>GS</sub> = 0V<br>V <sub>DS</sub> = 0.8 • V <sub>DSS</sub> | 120  | pF        |
| <b>C<sub>o(tr)</sub></b>            | Time related                                                                                                                                                                    |                                                                  | 375  | pF        |
| <b>t<sub>d(on)</sub></b>            | <b>Resistive Switching Times</b><br>V <sub>GS</sub> = 10V, V <sub>DS</sub> = 0.5 • V <sub>DSS</sub> , I <sub>D</sub> = 0.5 • I <sub>D25</sub><br>R <sub>G</sub> = 5Ω (External) |                                                                  | 21   | ns        |
| <b>t<sub>r</sub></b>                |                                                                                                                                                                                 |                                                                  | 43   | ns        |
| <b>t<sub>d(off)</sub></b>           |                                                                                                                                                                                 |                                                                  | 58   | ns        |
| <b>t<sub>f</sub></b>                |                                                                                                                                                                                 |                                                                  | 33   | ns        |
| <b>Q<sub>g(on)</sub></b>            | V <sub>GS</sub> = 10V, V <sub>DS</sub> = 0.5 • V <sub>DSS</sub> , I <sub>D</sub> = 0.5 • I <sub>D25</sub>                                                                       |                                                                  | 56   | nC        |
| <b>Q<sub>gs</sub></b>               |                                                                                                                                                                                 |                                                                  | 12   | nC        |
| <b>Q<sub>gd</sub></b>               |                                                                                                                                                                                 |                                                                  | 28   | nC        |
| <b>R<sub>thJC</sub></b>             | TO-247 & TO-3P                                                                                                                                                                  |                                                                  |      | 0.25 °C/W |
| <b>R<sub>thCS</sub></b>             |                                                                                                                                                                                 |                                                                  | 0.25 | °C/W      |

#### Source-Drain Diode

| Symbol   | Test Conditions<br>( $T_J = 25^{\circ}\text{C}$ , Unless Otherwise Specified)  | Characteristic Values |      |       |
|----------|--------------------------------------------------------------------------------|-----------------------|------|-------|
|          |                                                                                | Min.                  | Typ. | Max   |
| $I_S$    | $V_{GS} = 0\text{V}$                                                           |                       |      | 30 A  |
| $I_{SM}$ | Repetitive, pulse Width Limited by $T_{JM}$                                    |                       |      | 120 A |
| $V_{SD}$ | $I_F = I_S$ , $V_{GS} = 0\text{V}$ , Note 1                                    |                       |      | 1.4 V |
| $t_{rr}$ | $I_F = 15\text{A}$ , $-di/dt = 100\text{A}/\mu\text{s}$<br>$V_R = 100\text{V}$ |                       | 145  | ns    |
| $Q_{RM}$ |                                                                                |                       | 860  | nC    |
| $I_{RM}$ |                                                                                |                       | 12   | A     |

Note 1. Pulse test,  $t \leq 300\mu\text{s}$ , duty cycle,  $d \leq 2\%$ .

#### PRELIMINARY TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

|                                                                                  |           |           |           |           |             |             |             |             |             |             |
|----------------------------------------------------------------------------------|-----------|-----------|-----------|-----------|-------------|-------------|-------------|-------------|-------------|-------------|
| IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: | 4,835,592 | 4,931,844 | 5,049,961 | 5,237,481 | 6,162,665   | 6,404,065B1 | 6,683,344   | 6,727,585   | 7,005,734B2 | 7,157,338B2 |
|                                                                                  | 4,860,072 | 5,017,508 | 5,063,307 | 5,381,025 | 6,259,123B1 | 6,534,343   | 6,710,405B2 | 6,759,692   | 7,063,975B2 |             |
|                                                                                  | 4,881,106 | 5,034,796 | 5,187,117 | 5,486,715 | 6,306,728B1 | 6,583,505   | 6,710,463   | 6,771,478B2 | 7,071,537   |             |

Fig. 1. Output Characteristics @  $T_J = 25^\circ\text{C}$

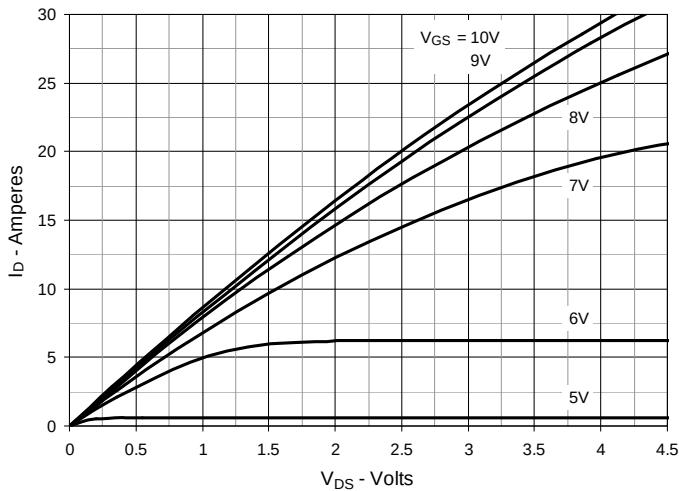


Fig. 2. Extended Output Characteristics @  $T_J = 25^\circ\text{C}$

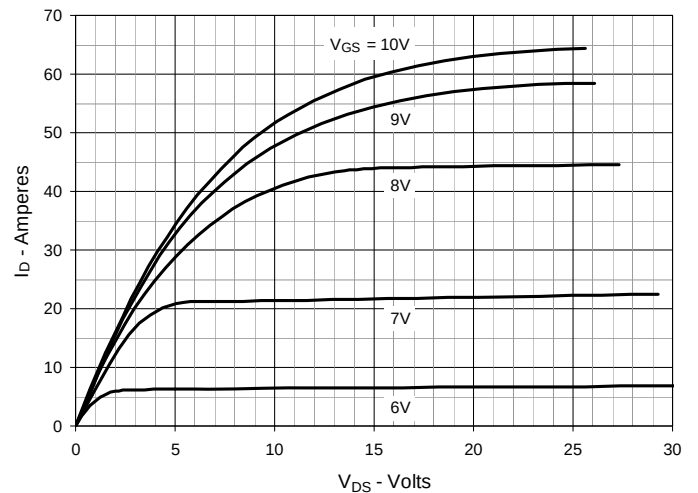


Fig. 3. Output Characteristics @  $T_J = 125^\circ\text{C}$

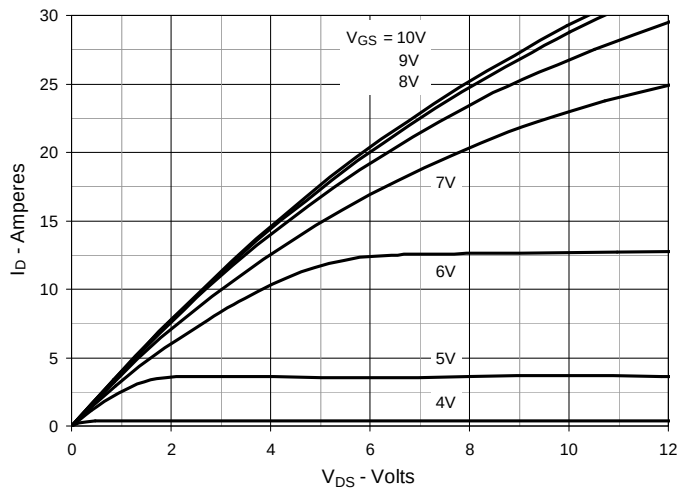


Fig. 4.  $R_{DS(on)}$  Normalized to  $I_D = 15A$  Value vs. Junction Temperature

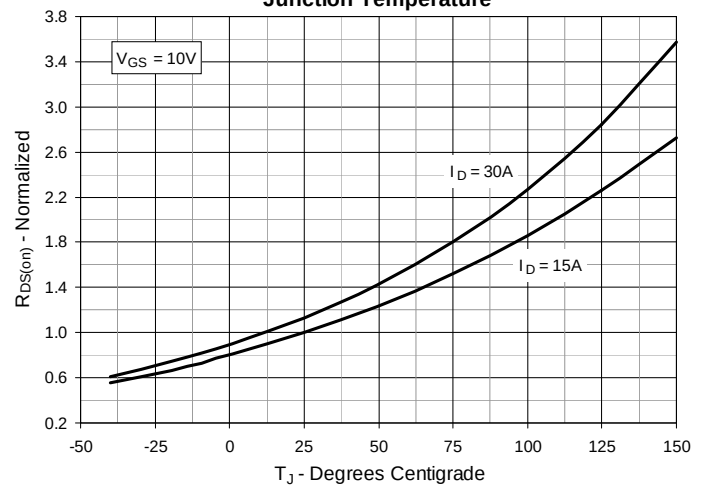


Fig. 5.  $R_{DS(on)}$  Normalized to  $I_D = 15A$  Value vs. Drain Current

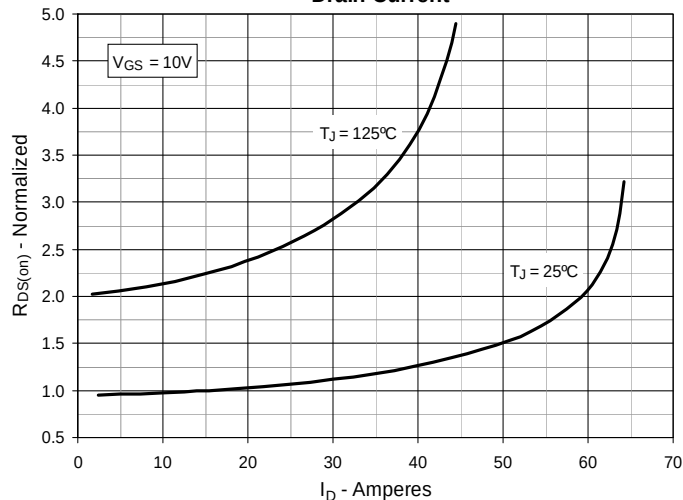
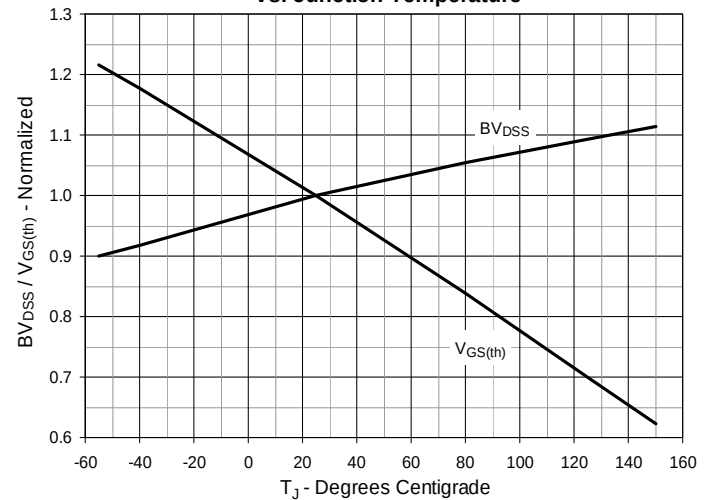
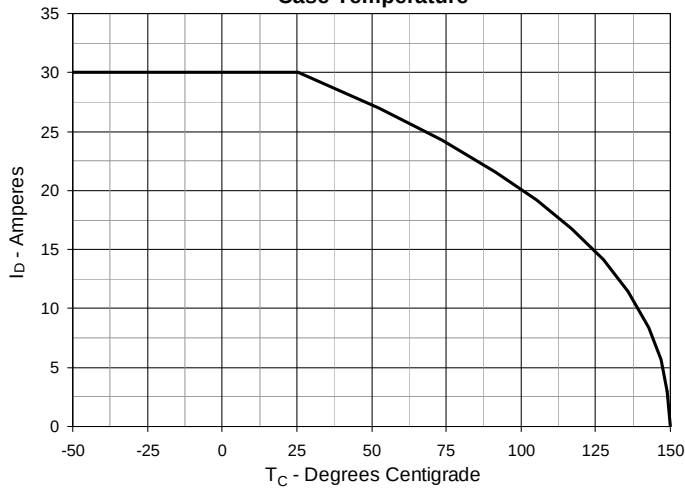


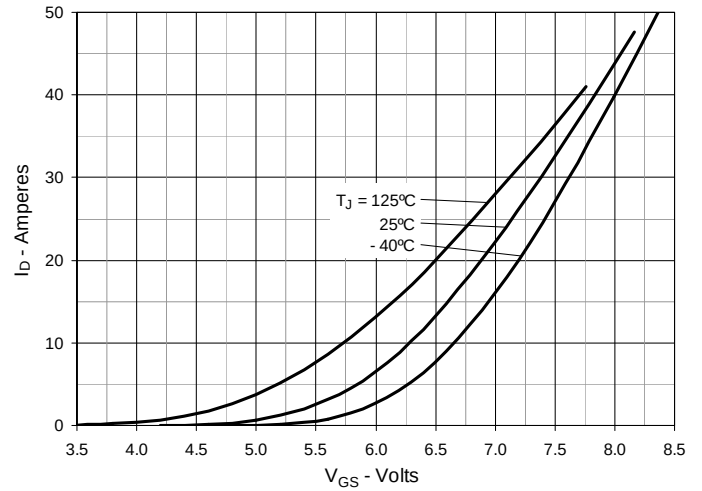
Fig. 6. Normalized Breakdown & Threshold Voltages vs. Junction Temperature



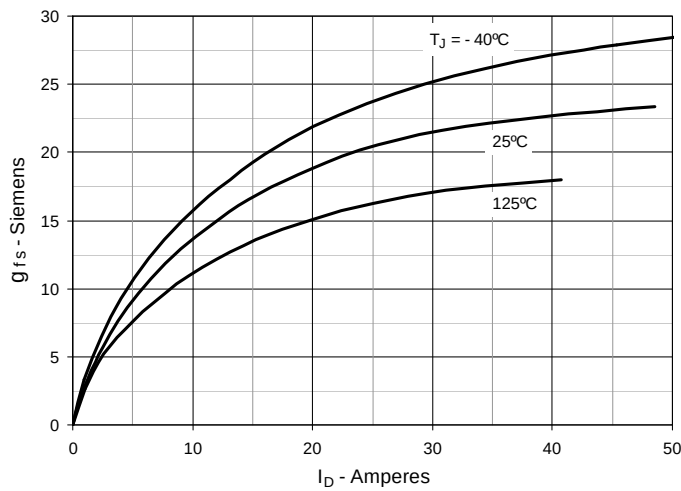
**Fig. 7. Maximum Drain Current vs. Case Temperature**



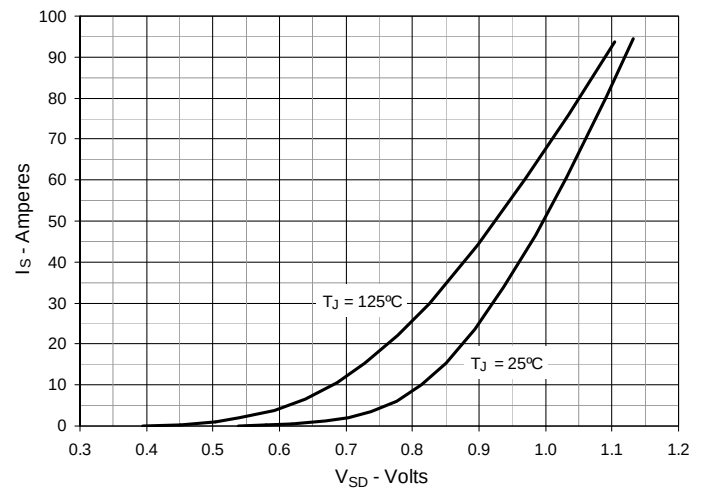
**Fig. 8. Input Admittance**



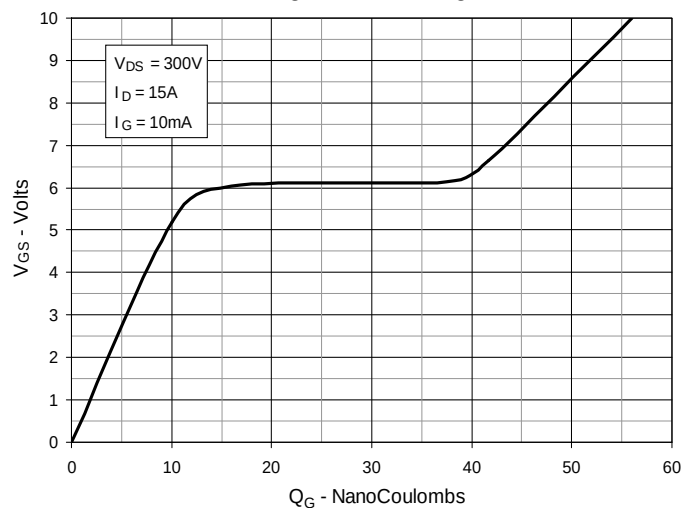
**Fig. 9. Transconductance**



**Fig. 10. Forward Voltage Drop of Intrinsic Diode**



**Fig. 11. Gate Charge**



**Fig. 12. Capacitance**

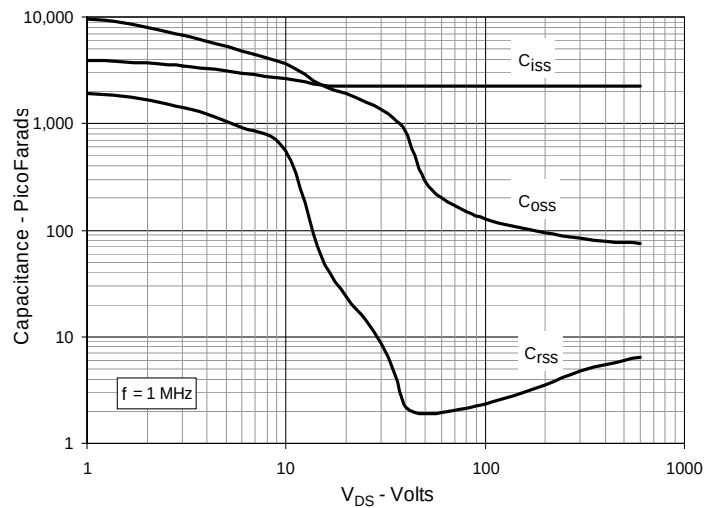


Fig. 13. Output Capacitance Stored Energy

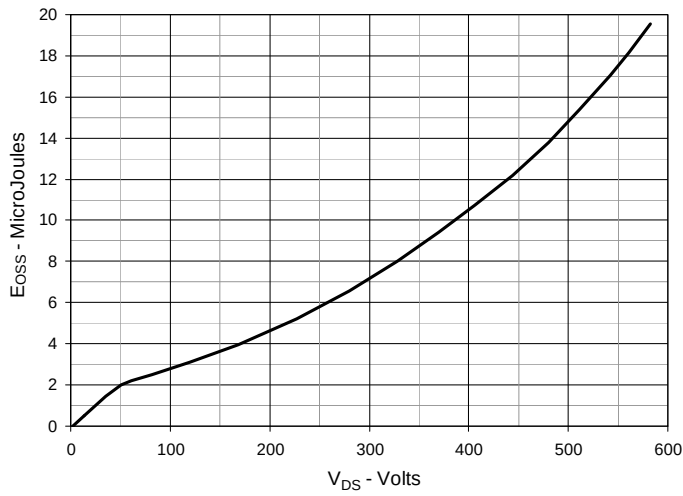


Fig. 14. Forward-Bias Safe Operating Area

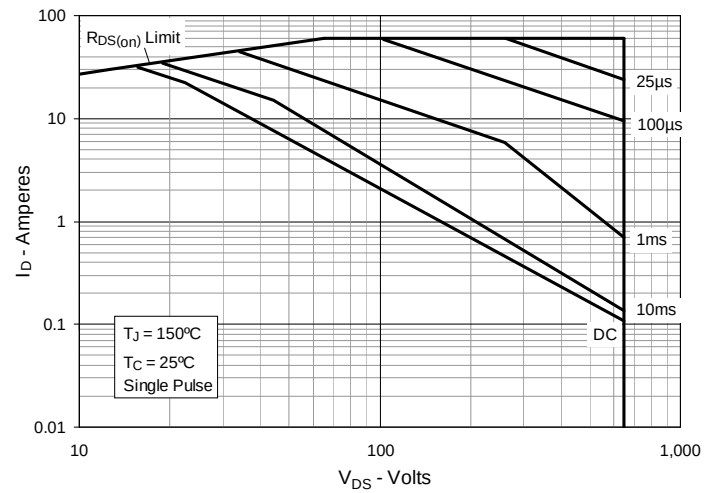
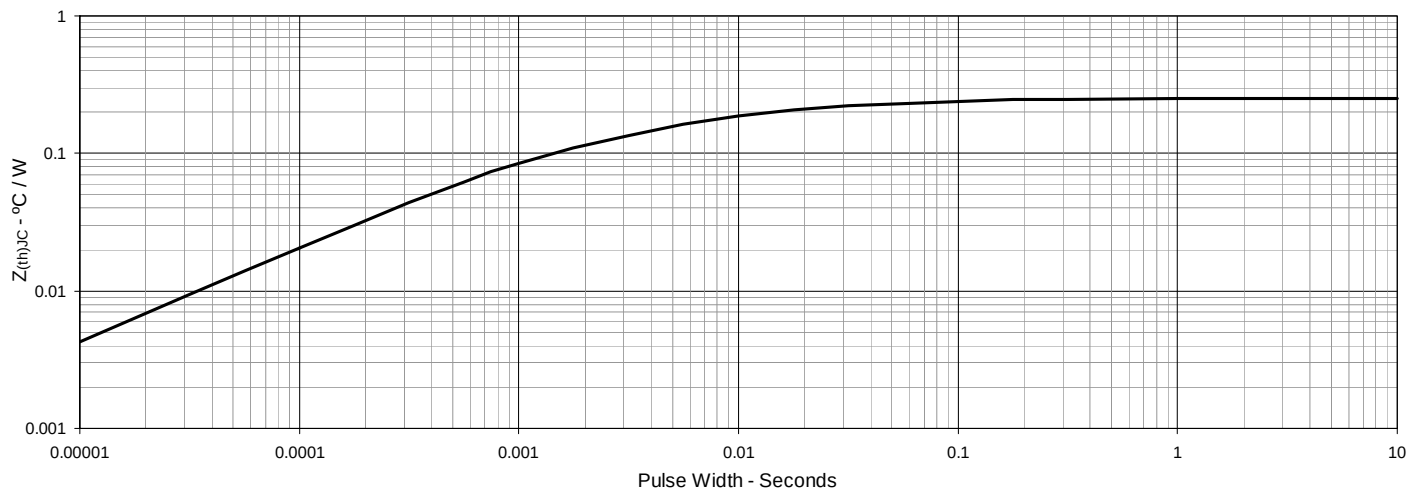


Fig. 15. Maximum Transient Thermal Impedance



| SYM | INCHES   |      | MILLIMETERS |       |
|-----|----------|------|-------------|-------|
|     | MIN      | MAX  | MIN         | MAX   |
| A   | .193     | .201 | 4.90        | 5.10  |
| A1  | .106     | .114 | 2.70        | 2.90  |
| A2  | .001     | .010 | 0.02        | 0.25  |
| B   | .045     | .057 | 1.15        | 1.45  |
| B2  | .075     | .083 | 1.91        | 2.10  |
| C   | .016     | .026 | 0.40        | 0.65  |
| C2  | .057     | .066 | 1.45        | 1.60  |
| D   | .543     | .551 | 13.80       | 14.00 |
| D1  | .488     | .500 | 12.40       | 12.70 |
| E   | .624     | .630 | 15.85       | 16.05 |
| E1  | .594     | .595 | 13.30       | 13.60 |
| ø   | .215 BSC |      | 5.45 BSC    |       |
| H   | .736     | .752 | 18.70       | 19.10 |
| L   | .094     | .106 | 2.40        | 2.70  |
| L1  | .047     | .055 | 1.20        | 1.40  |
| L2  | .039     | .045 | 1.00        | 1.15  |
| L3  | .010 BSC |      | 0.25 BSC    |       |
| L4  | .150     | .161 | 3.80        | 4.10  |

| SYM | INCHES   |      | MILLIMETERS |       |
|-----|----------|------|-------------|-------|
|     | MIN      | MAX  | MIN         | MAX   |
| A   | .185     | .193 | 4.70        | 4.90  |
| A1  | .051     | .059 | 1.30        | 1.50  |
| A2  | .057     | .065 | 1.45        | 1.65  |
| b   | .035     | .045 | 0.90        | 1.15  |
| b2  | .075     | .087 | 1.90        | 2.20  |
| b4  | .114     | .126 | 2.90        | 3.20  |
| c   | .022     | .031 | 0.55        | 0.80  |
| D   | .780     | .799 | 19.80       | 20.30 |
| D1  | .665     | .677 | 16.90       | 17.20 |
| E   | .610     | .622 | 15.50       | 15.80 |
| E1  | .531     | .539 | 13.50       | 13.70 |
| e   | .215 BSC |      | 5.45 BSC    |       |
| L   | .779     | .795 | 19.80       | 20.20 |
| L1  | .134     | .142 | 3.40        | 3.60  |
| ØP  | .126     | .134 | 3.20        | 3.40  |
| ØP1 | .272     | .280 | 6.90        | 7.10  |
| S   | .193     | .201 | 4.90        | 5.10  |

| SYM | INCHES   |      | MILLIMETERS |       |
|-----|----------|------|-------------|-------|
|     | MIN      | MAX  | MIN         | MAX   |
| A   | .190     | .205 | 4.83        | 5.21  |
| A1  | .090     | .100 | 2.29        | 2.54  |
| A2  | .075     | .085 | 1.91        | 2.16  |
| b   | .045     | .055 | 1.14        | 1.40  |
| b2  | .075     | .087 | 1.91        | 2.20  |
| b4  | .115     | .126 | 2.92        | 3.20  |
| C   | .024     | .031 | 0.61        | 0.80  |
| D   | .819     | .840 | 20.80       | 21.34 |
| D1  | .650     | .690 | 16.51       | 17.53 |
| D2  | .035     | .050 | 0.89        | 1.27  |
| E   | .620     | .635 | 15.75       | 16.13 |
| E1  | .545     | .565 | 13.84       | 14.35 |
| e   | .215 BSC |      | 5.45 BSC    |       |
| J   | --       | .010 | --          | 0.25  |
| K   | --       | .025 | --          | 0.64  |
| L   | .780     | .810 | 19.81       | 20.57 |
| L1  | .150     | .170 | 3.81        | 4.32  |
| øP  | .140     | .144 | 3.55        | 3.65  |
| øP1 | .275     | .290 | 6.99        | 7.37  |
| Q   | .220     | .244 | 5.59        | 6.20  |
| R   | .170     | .190 | 4.32        | 4.83  |
| S   | .242 BSC |      | 6.15 BSC    |       |



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